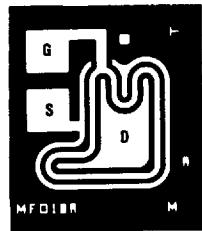


PRODUCT CATALOG

N-CHANNEL MOS FET

CHIP NUMBER
FMN1.1



0.023"
(0.581mm)

0.021"
(0.533mm)

Die Size: 21 x 23 (mils)
0.530 x 0.534 (mils)
Pad Size: 4 x 4 (mils)
BODY-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

- It is advisable that:
- a) the die be eutectically mounted with gold silicon preform 98/2%.
 - b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

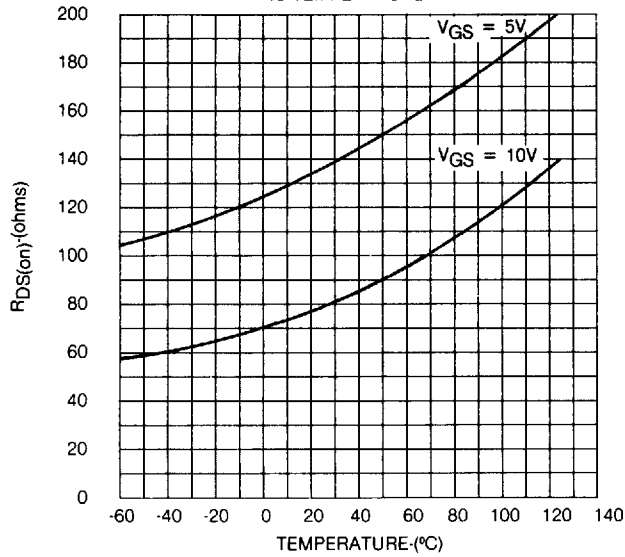
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVDSS	25	30		V	$I_D = +10 \mu A, V_{GS} = 0, V_{BS} = 0$
IDSS		10	500	pA	$V_{DS} = +15V, V_{GS} = 0, V_{BS} = 0$
gfs	1000	2500	4000	μmho	$V_{DS} = +15V, I_D = 2mA, f = 1KHz$
IGSS		0.1	10	pA	$V_{GS} = \pm 40V, V_{DS} = 0$
rDS(on)		60	195	Ω	$V_{DS} = 20V, I_D = 10mA, V_{BS} = 0$
VGS(Th)	+ .5	+ 1.5	+ 5.0	V	$V_{DS} = +15V, I_D = +10mA, V_{BS} = 0$
Crss		1.0	1.3	pF	$V_{DS} = +15V, I_D = +10mA, f = 1MHz$
Ciss		4.5	5	pF	$V_{DS} = +15V, I_D = 10mA, f = 1KHz$

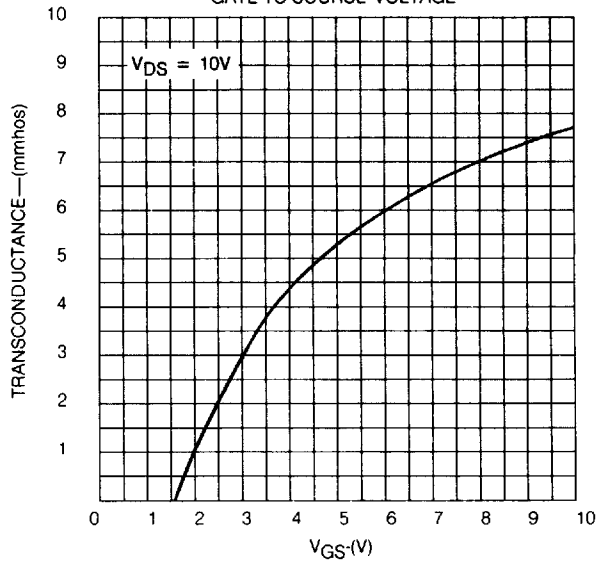
TYPICAL DEVICE TYPES: 3N169, 3N170, 3N171

CHIP TYPE FMN1.1

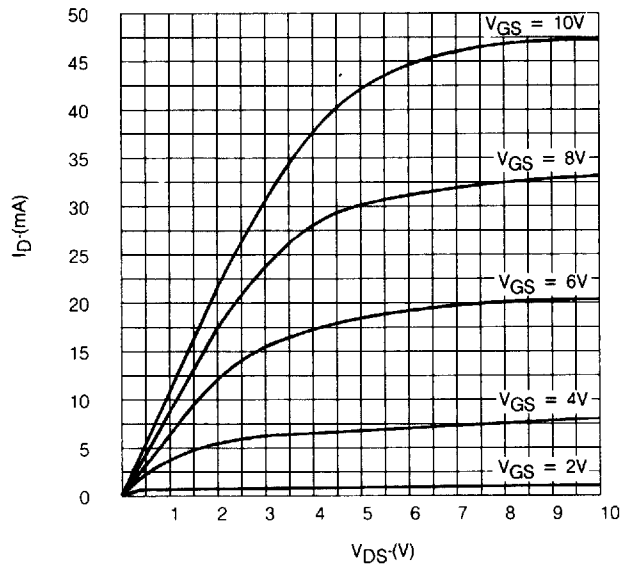
DRAIN-TO-SOURCE RESISTANCE
vs TEMPERATURE



TRANSCONDUCTANCE vs
GATE-TO-SOURCE VOLTAGE



DRAIN CURRENT vs
DRAIN-TO-SOURCE VOLTAGE



DRAIN CURRENT vs
GATE-TO-SOURCE VOLTAGE

